MOSFET – Power, Single N-Channel

80 V, 48 A, 14.5 mΩ

NTTFS6H854N

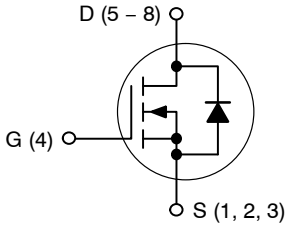
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
80 V	14.5 mΩ @ 10 V	48 A

WDFN8
(μ8FL)
CASE 511AB

Features

- Small Footprint (3.3 x 3.3 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- These Devices are Pb−Free and are RoHS Compliant

N−Channel



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Symbol	Parameter			Value	Unit
V_{DSS}	Drain−to−Source Voltage			80	V
V_{GS}	Gate−to−Source Voltage			±20	V
I_D	Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3, 4)	Steady State	T_C = 25°C	44	A
			T_C = 100°C	31	
P_D	Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3)		T_C = 25°C	68	W
			T_C = 100°C	34	
I_D	Continuous Drain Current $R_{\theta JA}$ (Notes 1, 3, 4)	Steady State	T_A = 25°C	9.5	A
			T_A = 100°C	6.7	
P_D	Power Dissipation $R_{\theta JA}$ (Notes 1, 3)		T_A = 25°C	3.2	W
			T_A = 100°C	1.6	
I_{DM}	Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		175	A
T_J, T_{stg}	Operating Junction and Storage Temperature Range			−55 to +175	°C
I_S	Source Current (Body Diode)			57	A
E_{AS}	Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 2.2 A)			205	mJ
T_L	Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			260	°C

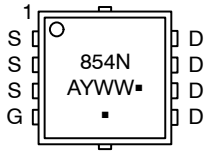
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction−to−Case − Steady State (Note 3)	2.2	°C/W
$R_{\theta JA}$	Junction−to−Ambient − Steady State (Note 3)	47	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51−12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface−mounted on FR4 board using a 650 mm^2, 2 oz. Cu pad.
4. Continuous DC current rating. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

MARKING DIAGRAM



854N = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
$V_{(BR)DSS}$	Drain−to−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA		80			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0 V, V_{DS} = 80 V	T_J = 25°C			10	μA
			T_J = 125°C			250	
I_{GSS}	Gate−to−Source Leakage Current	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 5)							
$V_{GS(TH)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 45 μA		2.0		4.0	V
$R_{DS(on)}$	Drain−to−Source On Resistance	V_{GS} = 10 V, I_D = 10 A			11.9	14.5	mΩ
		V_{GS} = 6 V, I_D = 10 A			17.1	23.1	
g_{FS}	Forward Transconductance	V_{DS} = 15 V, I_D = 15 A			39.5		S
CHARGES AND CAPACITANCES							
C_{iss}	Input Capacitance	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 40 V			770		pF
C_{oss}	Output Capacitance				113		
C_{rss}	Reverse Transfer Capacitance				5.4		
$Q_{G(TH)}$	Threshold Gate Charge	V_{GS} = 10 V, V_{DS} = 40 V, I_D = 15 A			2.7		nC
Q_{GS}	Gate−to−Source Charge				4.3		
Q_{GD}	Gate−to−Drain Charge				2.3		
$Q_{G(TOT)}$	Total Gate Charge	V_{GS} = 10 V, V_{DS} = 40 V, I_D = 15 A			13		nC
SWITCHING CHARACTERISTICS (Note 6)							
$t_{d(on)}$	Turn−On Delay Time	V_{GS} = 6.0 V, V_{DS} = 64 V, I_D = 15 A			11		ns
t_r	Rise Time				22		
$t_{d(off)}$	Turn−Off Delay Time				24		
t_f	Fall Time				6.0		
DRAIN−SOURCE DIODE CHARACTERISTICS							
V_{SD}	Forward Diode Voltage	V_{GS} = 0 V, I_S = 10 A	T_J = 25°C		0.8	1.2	V
			T_J = 125°C		0.7		
t_{RR}	Reverse Recovery Time	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 15 A			33		ns
t_a	Charge Time				22		
t_b	Discharge Time				11		
Q_{RR}	Reverse Recovery Charge				29		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

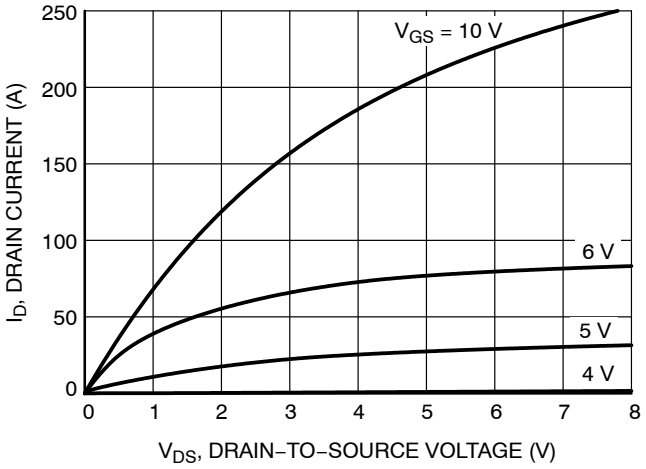


Figure 1. On−Region Characteristics

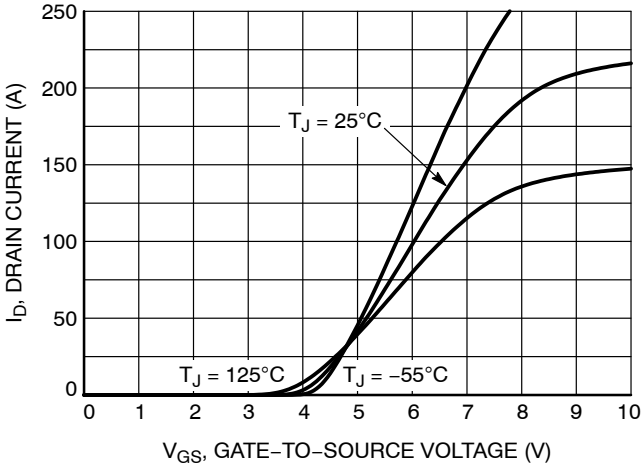


Figure 2. Transfer Characteristics

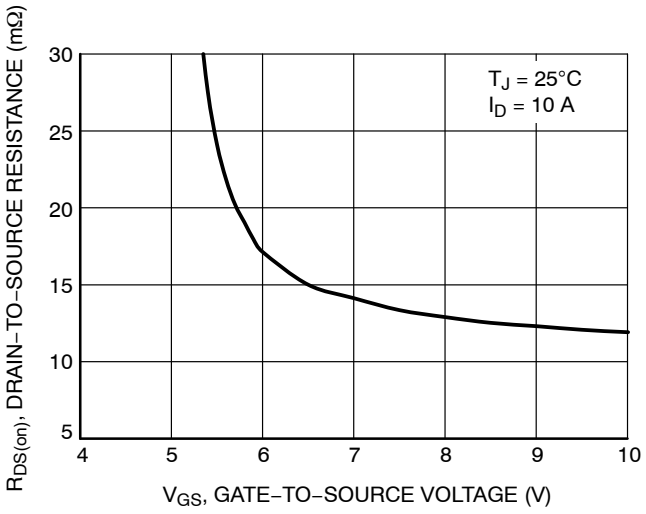


Figure 3. On−Resistance vs. Gate−to−Source Voltage

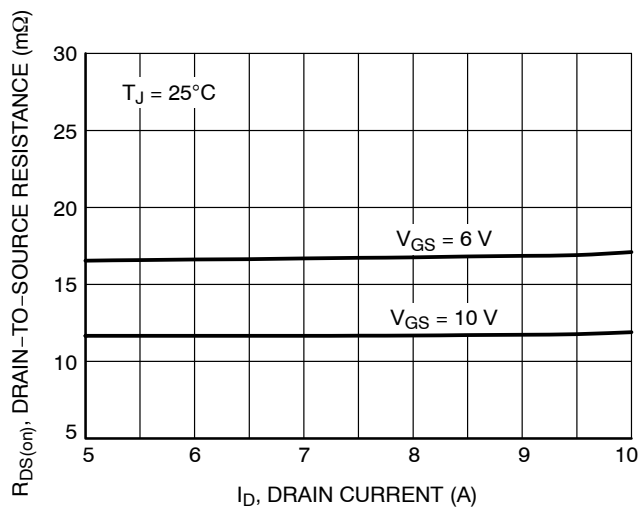


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

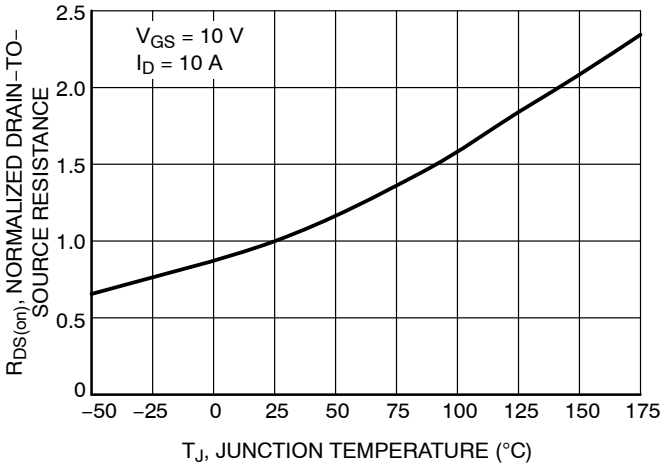


Figure 5. On−Resistance Variation with Temperature

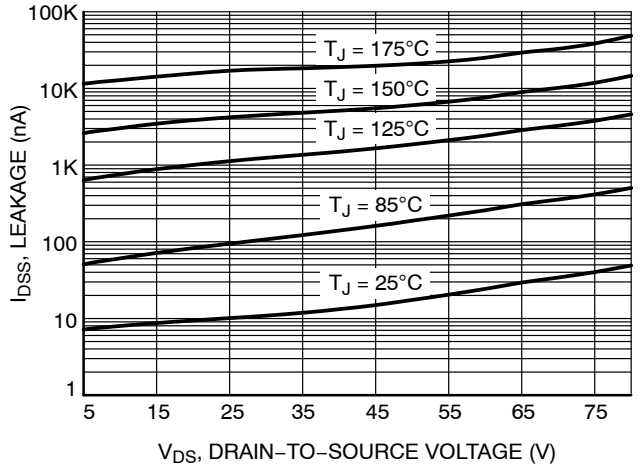


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

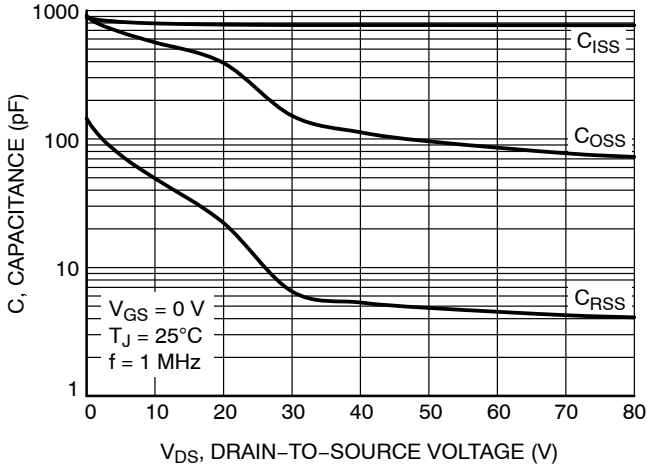


Figure 7. Capacitance Variation

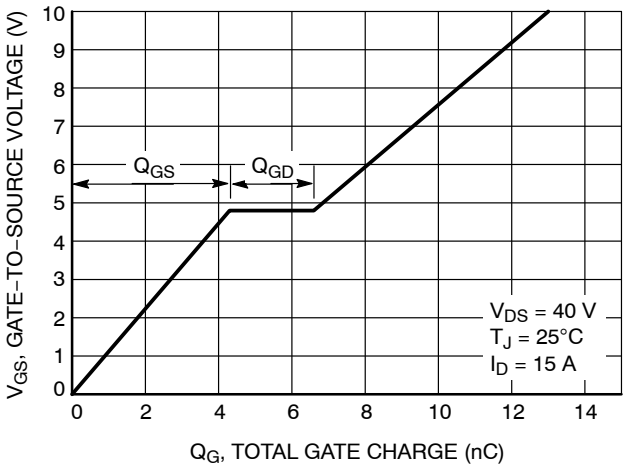


Figure 8. Gate−to−Source Voltage vs. Total Charge

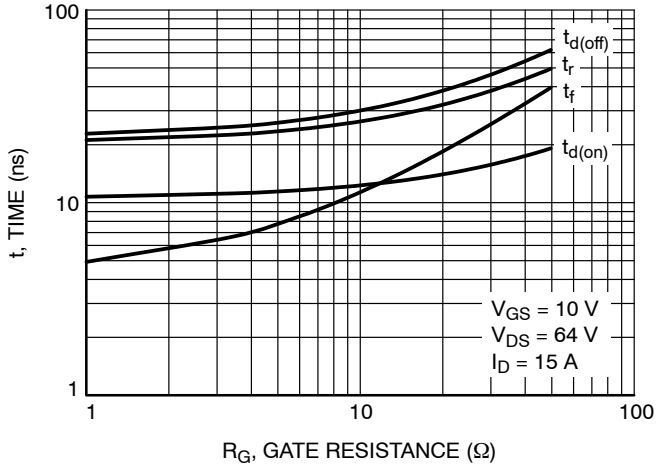


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

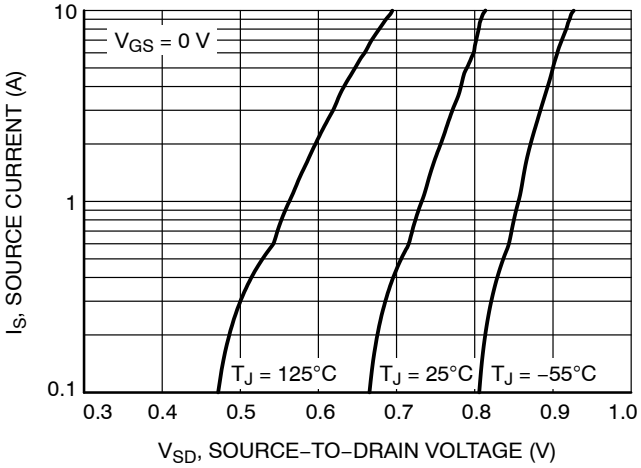


Figure 10. Diode Forward Voltage vs. Current

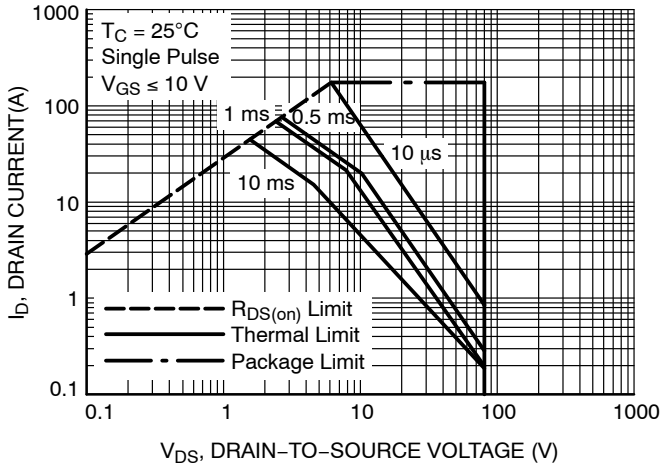


Figure 11. Maximum Rated Forward Biased Safe Operating Area

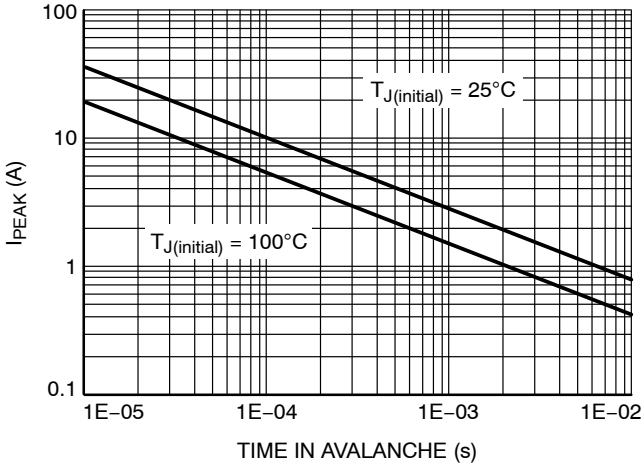


Figure 12. I_{PEAK} vs. Time in Avalanche

TYPICAL CHARACTERISTICS (continued)

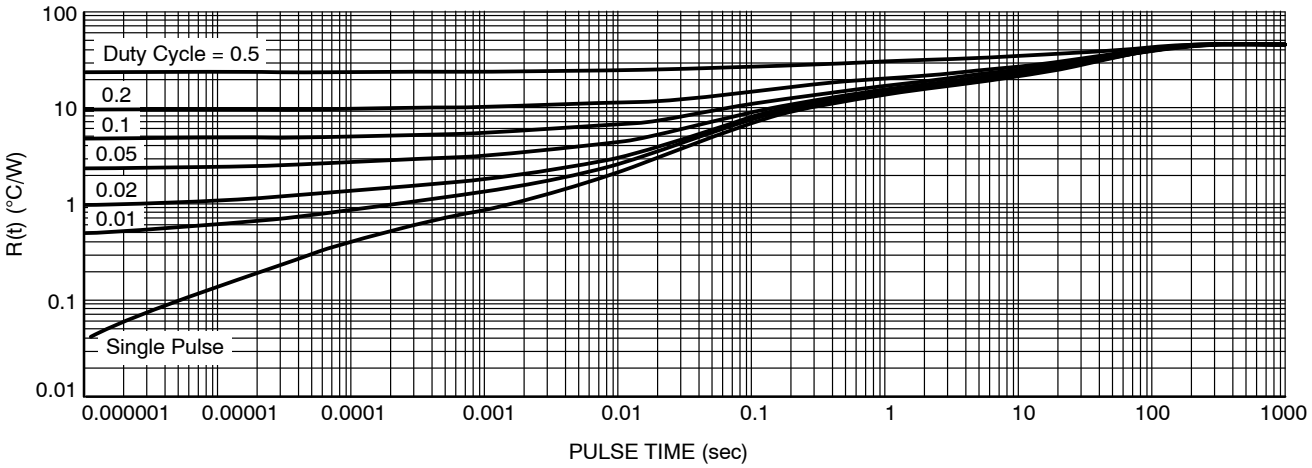


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

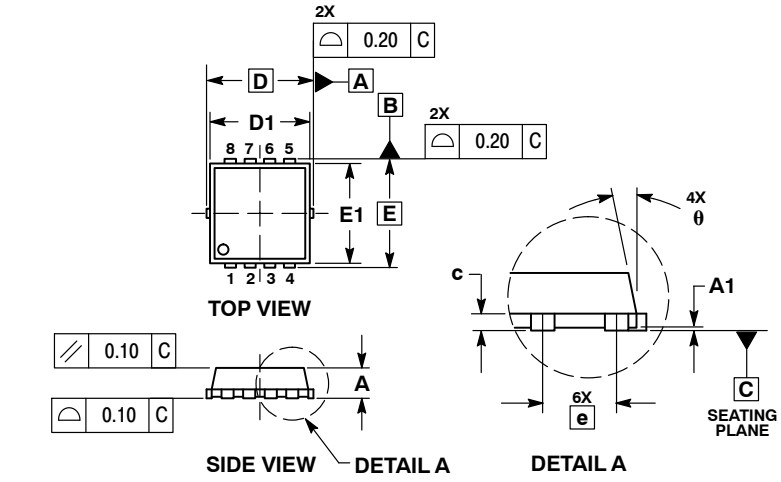
Device	Marking	Package	Shipping†
NTTFS6H854NTAG	854N	WDFN8 (Pb−Free)	1,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SCALE 2:1

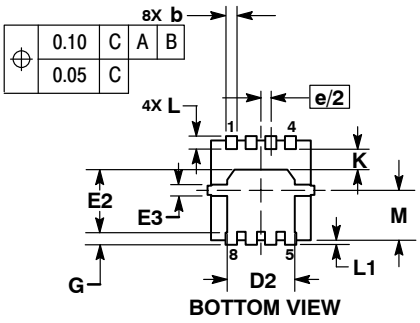
WDFN8 3.3x3.3, 0.65P
CASE 511AB
ISSUE D

DATE 23 APR 2012



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	---	0.05	0.000	---	0.002
b	0.23	0.30	0.40	0.009	0.012	0.016
c	0.15	0.20	0.25	0.006	0.008	0.010
D		3.30 BSC			0.130 BSC	
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
E		3.30 BSC			0.130 BSC	
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	0.23	0.30	0.40	0.009	0.012	0.016
e		0.65 BSC			0.026 BSC	
G	0.30	0.41	0.51	0.012	0.016	0.020
K	0.65	0.80	0.95	0.026	0.032	0.037
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
M	1.40	1.50	1.60	0.055	0.059	0.063
θ	0 °	---	12 °	0 °	---	12 °

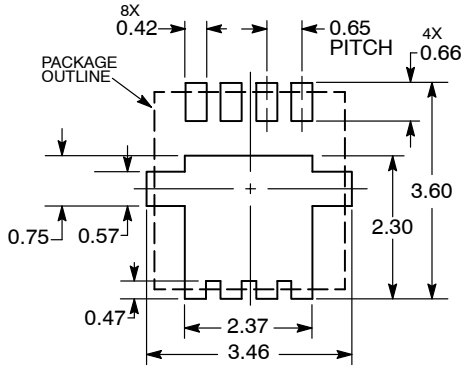


GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	**98AON30561E**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**WDFN8 3.3X3.3, 0.65P**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

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For additional information, please contact your local Sales Representative at
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